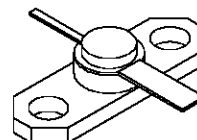


RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

- EMITTER BALLASTED
- VSWR CAPABILITY $\infty:1$ @ RATED CONDITIONS
- REFRACTORY/GOLD METALLIZATION
- HERMETIC STRIPAC[®] PACKAGE
- $P_{OUT} = 3.0$ W MIN. WITH 7.8 dB GAIN @ 2.0 GHz



.250 2LFL (S010)
hermetically sealed

ORDER CODE

MSC82003

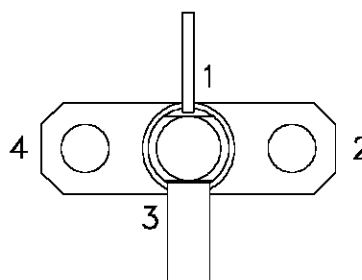
BRANDING

82003

DESCRIPTION

The MSC82003 is a common base hermetically sealed silicon NPN microwave transistor utilizing a fishbone emitter ballasted geometry with a refractory/gold metallization system. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions. The MSC82003 was designed for Class C amplifier applications in the 1.0 - 2.0 GHz frequency range.

PIN CONNECTION



1. Collector

2. Base

3. Emitter

4. Base

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation*	21.8	W
I_C	Device Current*	600	mA
V_{CC}	Collector-Supply Voltage*	35	V
T_J	Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +200	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	8.0	$^{\circ}\text{C/W}$
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*Applies only to rated RF amplifier operation

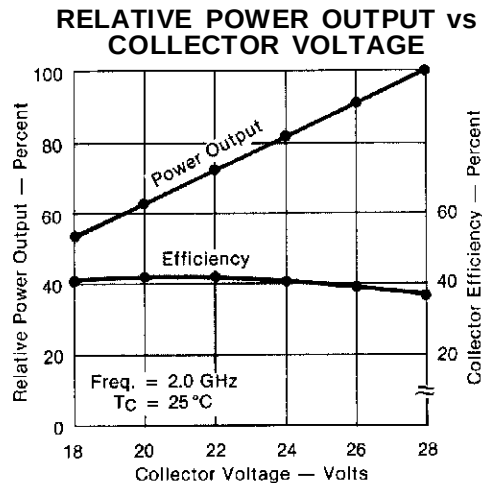
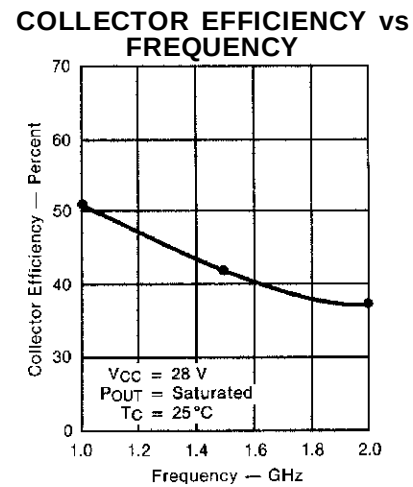
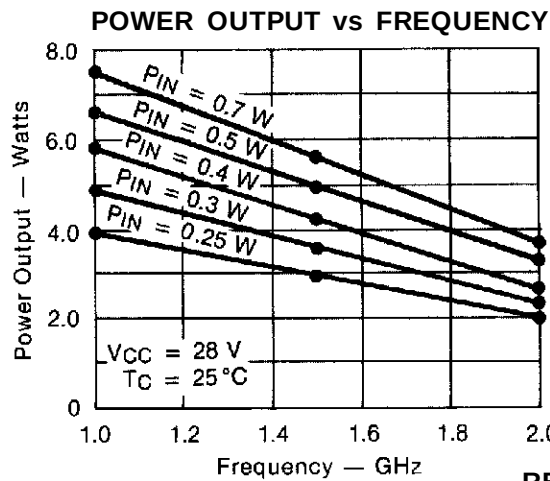
ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

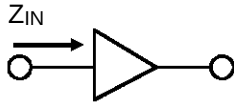
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	$I_C = 1\text{mA}$ $I_E = 0\text{mA}$	45	—	—	V
BV_{EBO}	$I_E = 1\text{mA}$ $I_C = 0\text{mA}$	3.5	—	—	V
BV_{CER}	$I_C = 5\text{mA}$ $R_{BE} = 10\Omega$	45	—	—	V
I_{CBO}	$V_{CB} = 28\text{V}$	—	—	1.0	mA
h_{FE}	$V_{CE} = 5\text{V}$ $I_C = 200\text{mA}$	15	—	120	—

DYNAMIC

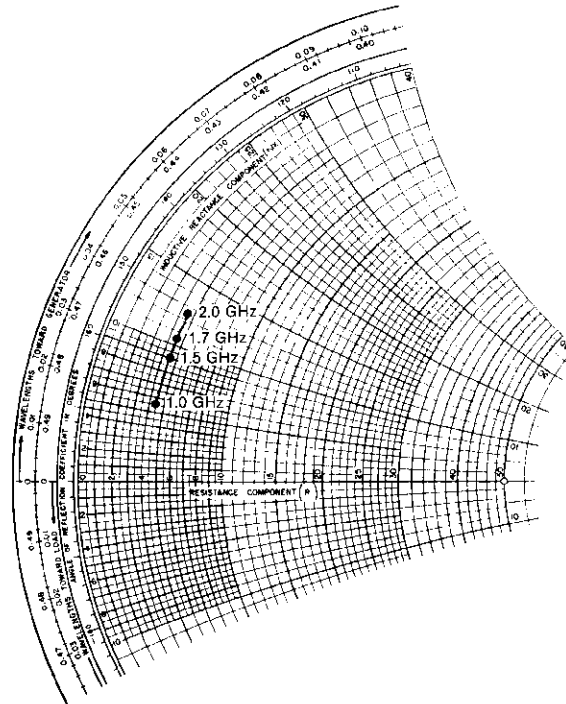
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	$f = 2.0\text{ GHz}$ $P_{IN} = 0.5\text{ W}$ $V_{CC} = 28\text{ V}$	3.0	3.3	—	W
η_c	$f = 2.0\text{ GHz}$ $P_{IN} = 0.5\text{ W}$ $V_{CC} = 28\text{ V}$	35	37	—	%
G_P	$f = 2.0\text{ GHz}$ $P_{IN} = 0.5\text{ W}$ $V_{CC} = 28\text{ V}$	7.8	8.2	—	dB
C_{OB}	$f = 1\text{ MHz}$ $V_{CB} = 28\text{ V}$	—	—	6.5	pF

TYPICAL PERFORMANCE


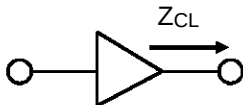
IMPEDANCE DATA

TYPICAL INPUT
IMPEDANCE

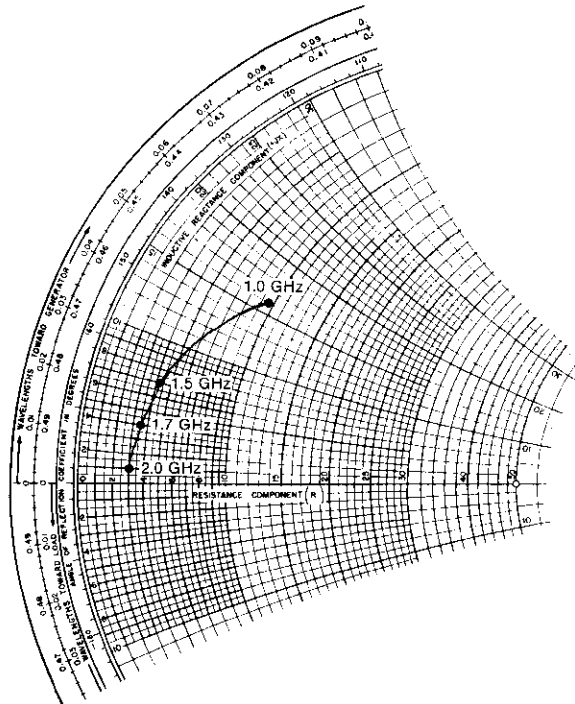
$P_{IN} = 0.5 \text{ W}$
 $V_{CC} = 28 \text{ V}$
 Normalized to 50 ohms



FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
1.0 GHz	$4.4 + j 5.5$	$9.6 + j 16.0$
1.5 GHz	$4.5 + j 9.0$	$4.3 + j 7.0$
1.7 GHz	$4.5 + j 10.5$	$3.5 + j 4.0$
2.0 GHz	$4.6 + j 12.5$	$3.0 + j 1.0$

TYPICAL COLLECTOR
LOAD IMPEDANCE

$P_{OUT} = \text{Saturated}$
 $V_{CC} = 28 \text{ V}$
 Normalized to 50 ohms



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